

ISL71610x

Neutron Testing of the ISL71610x Passive-Input Digital Isolator

Introduction

This report summarizes the 1MeV equivalent neutron testing results of the [ISL71610SLHM](#) and [ISL71610M](#) passive-input digital signal isolator with a CMOS output. The test was conducted to determine the sensitivity of the part to displacement damage (DD) caused by neutron or proton environments. Neutron fluences ranged from $5 \times 10^{11} \text{n/cm}^2$ to $1 \times 10^{13} \text{n/cm}^2$.

Product Description

The ISL71610x is a passive-input digital signal isolator with a CMOS output. It has a similar interface as traditional optocouplers but has better performance and higher package density.

The ISL71610x is manufactured with Giant Magnetoresistive (GMR) technology for small size, high speed, and low power. A ceramic/polymer composite barrier provides excellent isolation and an unlimited barrier life. A series external resistor sets the input coil current, and a capacitor in parallel with the current-limiting resistor provides improved dynamic performance. This versatile component can replace various optocouplers and function over a wide range of data rates, edge speeds, and power supply levels. The device output is compatible with 3.3V and 5V supplies, allowing an interface to the controller without additional level shifting. With the coil energized with a minimum of $\pm 8 \text{mA}$ (bidirectional current), the ISL71610x is suitable for single-ended and differential drive applications.

The ISL71610x is offered in an 8 Ld 5mm×4mm SNOIC package and is fully specified across the military ambient temperature range of -55°C to $+125^\circ\text{C}$.

The pin assignments for the ISL71610x are shown in [Figure 1](#), and the pin descriptions are in [Table 1](#).

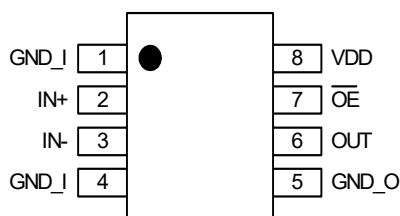


Figure 1. Pin Assignments

Table 1. ISL71610x Pin Descriptions

| Pin Number | Pin Name | Description |
|------------|----------|--|
| 1, 4 | GND_I | No internal connection. Use for input shielding, connect to input side ground. |
| 2 | IN+ | Coil connection. The voltage applied to IN+ is more negative than IN- to cause the voltage of OUT to switch to V_{OL} (logic low). |
| 3 | IN- | Coil connection. The voltage applied to IN- is more positive than IN+ to cause the voltage of OUT to switch to V_{OL} (logic low). |
| 5 | GND_O | Ground return for V_{DD} |
| 6 | OUT | Data output. The OUT pin logic high is the zero input current state. |

Table 1. ISL71610x Pin Descriptions (Cont.)

| Pin Number | Pin Name | Description |
|------------|-----------------|--|
| 7 | \overline{OE} | Output enable, active low. Internally pulled low with 100kΩ to enable the output when this pin is not connected. |
| 8 | VDD | Receiver supply voltage. |

Contents

| | |
|---|-----------|
| 1. Test Description | 3 |
| 1.1 Irradiation Facilities | 3 |
| 1.2 4.2 Test Fixturing | 3 |
| 1.3 Radiation Dosimetry | 3 |
| 1.4 Characterization equipment and procedures | 3 |
| 1.5 Experimental Matrix | 3 |
| 2. Results | 4 |
| 2.1 Attributes Data | 4 |
| 2.2 Key Parameter Variables Data | 4 |
| 3. Discussion and Conclusion | 13 |
| 4. Revision History | 13 |
| A. Appendix | 14 |
| A.1 Reported Parameters | 14 |
| A.2 Related Information | 15 |

1. Test Description

1.1 Irradiation Facilities

Neutron fluence irradiations were performed on the test samples on March 29, 2023, at the University of Massachusetts, Lowell (UMASS Lowell) fast neutron irradiator per Mil-STD-883G, Method 1017.2, with each part unpowered during irradiation. The target irradiation levels were $5 \times 10^{11} \text{n/cm}^2$, $2 \times 10^{12} \text{n/cm}^2$, and $1 \times 10^{13} \text{n/cm}^2$. As neutron irradiation activates many heavier elements found in a packaged integrated circuit, the parts exposed at the higher neutron levels required (as expected) some cooldown time before being shipped back to Renesas (Palm Bay, FL) for electrical testing.

1.2 4.2 Test Fixturing

No formal irradiation test fixturing is involved, as these DD tests are bag tests in the sense that the parts are irradiated with all leads unbiased.

1.3 Radiation Dosimetry

Table 2 shows dosimetry from UMASS Lowell, indicating the total accumulated gamma dose and actual neutron fluence exposure levels for each set of samples.

Table 2. ISL71610x Neutron Fluence Dosimetry Data

| Irradiation | Requested Fluence (n/cm ²) | Reactor Power (kW) | Time (s) | Flux (n/cm ² -s) ^{[1][2]} | Gamma Dose (rad(Si)) ^[3] | Measured Fluence (n/cm ²) ^[4] |
|-------------|--|--------------------|----------|---|-------------------------------------|--|
| CRF#77981-B | 5.00E+11 | 50 | 131 | 3.83E+09 | 75 | 5.30E+11 |
| CRF#77981-C | 2.00E+12 | 80 | 327 | 6.12E+09 | 298 | 2.33E+12 |
| CRF#77981-D | 1.00E+13 | 1000 | 131 | 7.65E+10 | 1492 | 1.04E+13 |

1. Dosimetry method: ASTM E-265
2. The neutron fluence rate is determined from *Initial Testing of the New Ex-Core Fast Neutron Irradiator at UMass Lowell (6/18/02)*. Validated on 6/07/2011 under the Trident II D5LE neutron facility study by Navy Crane.
3. Based on reactor power at 1000kW, the gamma dose is $41 \pm 5.3\%$ krad(Si)/hr as mapped by TLD-based dosimetry.
4. Validated by S-32 flux monitors.

1.4 Characterization equipment and procedures

Electrical testing was performed before and after irradiation using the Renesas production automated test equipment (ATE). All electrical testing was performed at room temperature.

1.5 Experimental Matrix

Testing proceeded in general accordance with the guidelines of MIL-STD-883 TM 1017. The experimental matrix consisted of six samples to be irradiated at $5 \times 10^{11} \text{n/cm}^2$, six at $2 \times 10^{12} \text{n/cm}^2$, and six at $1 \times 10^{13} \text{n/cm}^2$. The actual levels achieved, shown in Table 3, were $5.3 \times 10^{11} \text{n/cm}^2$, $2.3 \times 10^{12} \text{n/cm}^2$, and $1 \times 10^{13} \text{n/cm}^2$. Two control units were used.

The 18 ISL71610x samples were drawn from Lot 212010. Samples were packaged in the standard 8 Ld 5mm×4mm SNOIC package. Samples were processed through burn-in before irradiation and screened to the datasheet limits at room, low, and high temperatures before neutron testing.

2. Results

Neutron testing of the ISL71610x is complete, and the results are reported in the balance of this report. It should be understood when interpreting the data that each neutron irradiation was performed on a different set of samples; this is not total dose testing, where the damage is cumulative.

2.1 Attributes Data

Table 3. ISL71610x Attributes Data

| 1MeV Fluence, (n/cm ²) | | Sample Size | Pass ^[1] | Fail | Notes |
|------------------------------------|-----------------------|-------------|---------------------|------|------------|
| Planned | Actual | | | | |
| 5×10 ¹¹ | 5.30×10 ¹¹ | 6 | 6 | 0 | All passed |
| 2×10 ¹² | 2.33×10 ¹² | 6 | 6 | 0 | All passed |
| 1×10 ¹³ | 1.04×10 ¹³ | 6 | 6 | 0 | All passed |

1. A Pass indicates a sample that passes all post-irradiation datasheet limits.

2.2 Key Parameter Variables Data

The plots in Figure 2 through Figure 18 show data plots for key parameters before and after irradiation to each level. The plots show the mean of each parameter as a function of neutron irradiation. The plots also include error bars at each down-point, representing the minimum and maximum measured values of the samples, although, in some plots, the error bars might not be visible due to their values compared to the scale of the graph. While the applicable electrical limits taken from the datasheet are also shown, it should be noted that these limits are provided for guidance only as the ISL71610x is not specified for the neutron environment.

All samples passed the post-irradiation datasheet limits after all three exposures up to and including 1.04×10¹³n/cm².

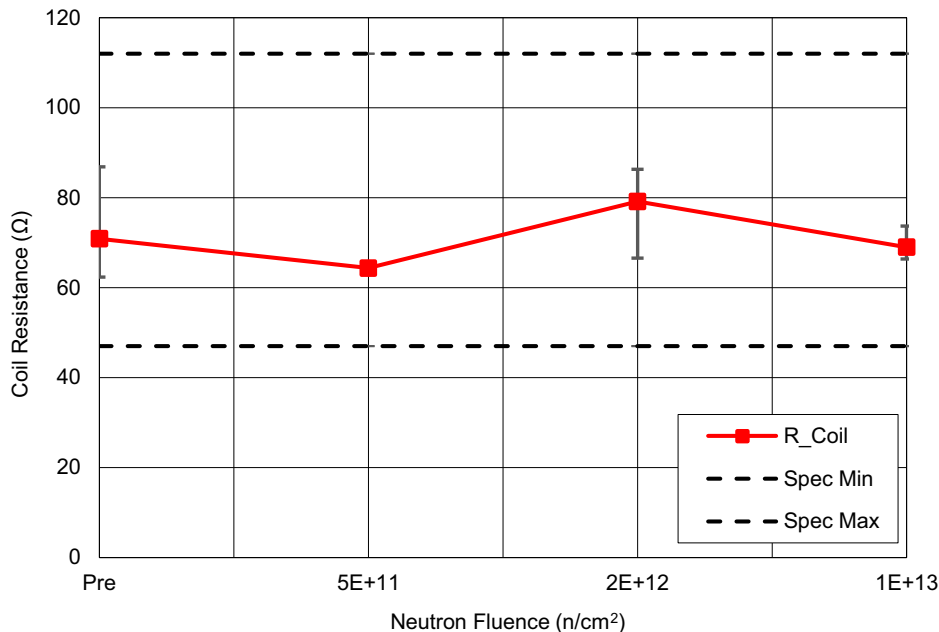


Figure 2. ISL71610x average coil resistance (R_{COIL}) as a function of neutron fluence. The error bars represent the minimum and maximum measured values. The datasheet limits are 47Ω minimum and 112Ω maximum.

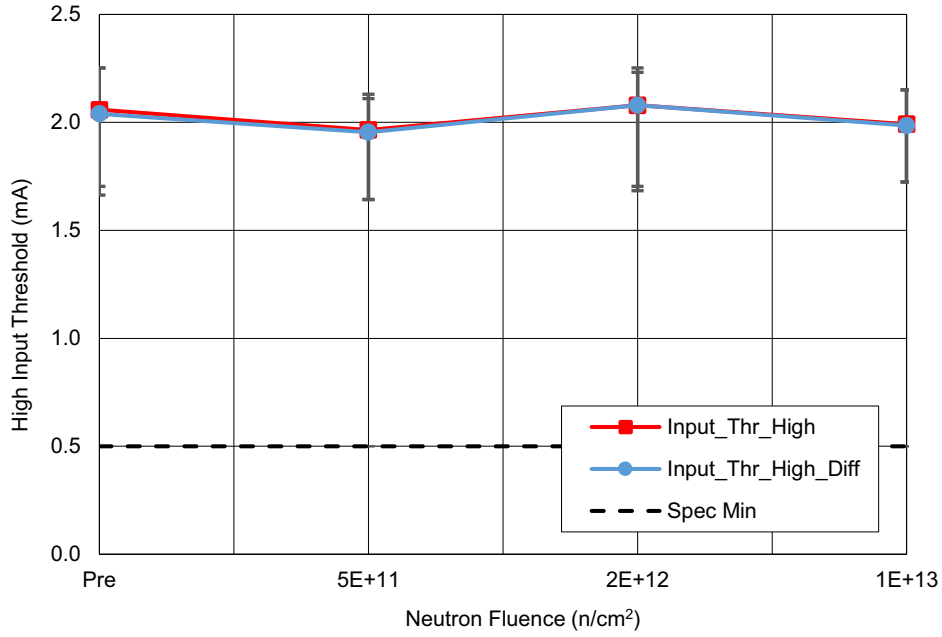


Figure 3. ISL71610x average high input threshold, DC single ended (I_{INH-DC}) and differential ($I_{INH-DIFF}$) as a function of neutron fluence. The error bars represent the minimum and maximum measured values. The datasheet limit is 0.5mA minimum.

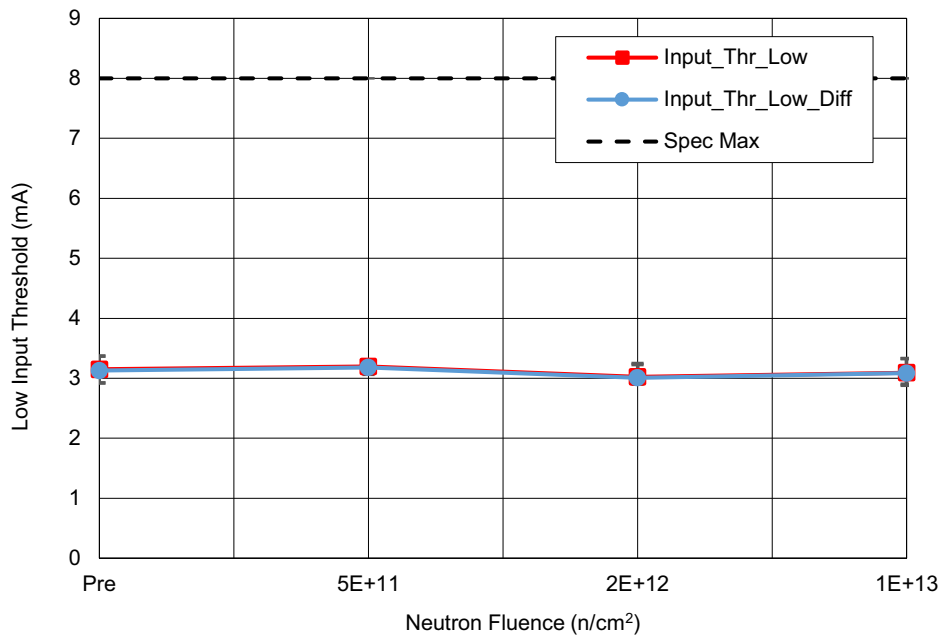


Figure 4. ISL71610x average low input threshold, DC single ended (I_{INL-DC}) and differential ($I_{INL-DIFF}$) as a function of neutron fluence. The error bars represent the minimum and maximum measured values. The datasheet limit is 8mA maximum.

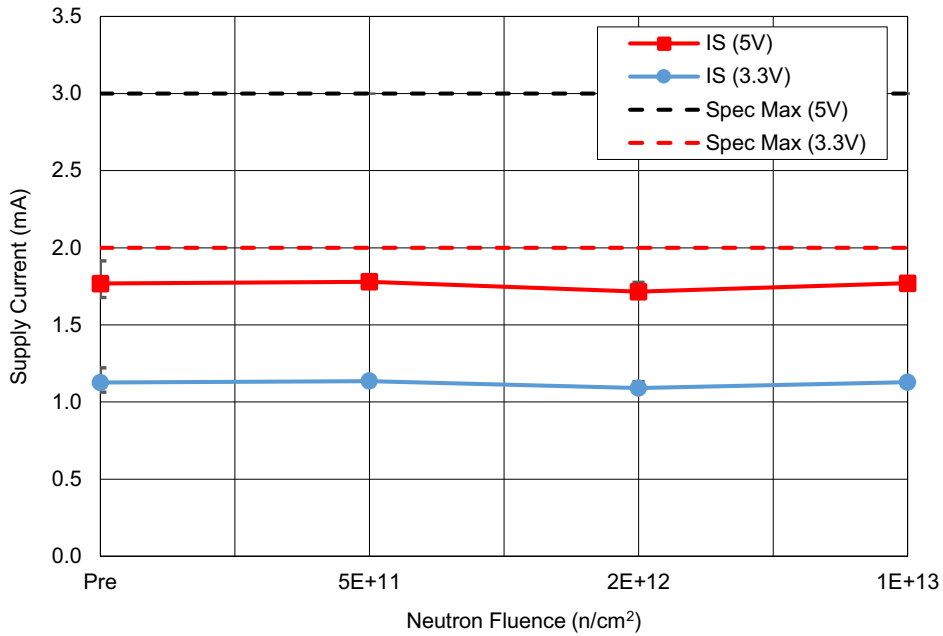


Figure 5. ISL71610x average quiescent current (I_{DDQ}) with $V_{DD} = 5.0V$ and $3.3V$ and $IN+ = IN- = OPEN$ as a function of neutron fluence. The error bars represent the minimum and maximum measured values. The datasheet limit is 2mA maximum for 3.3V and 3mA maximum for 5V.

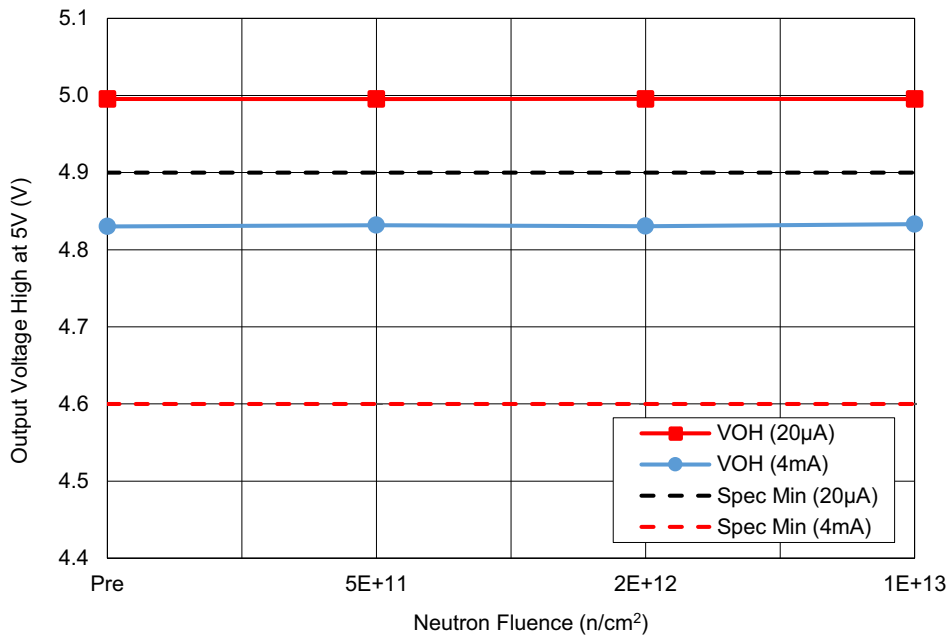


Figure 6. ISL71610x average output voltage high (V_{OH}) with $V_{DD} = 5V$ and $I_{OUT} = 20\mu A$ and $4mA$ as a function of neutron fluence. The error bars (if visible) represent the minimum and maximum measured values. The datasheet limit is 4.9V minimum for $20\mu A$ and 4.6V minimum for $4mA$.

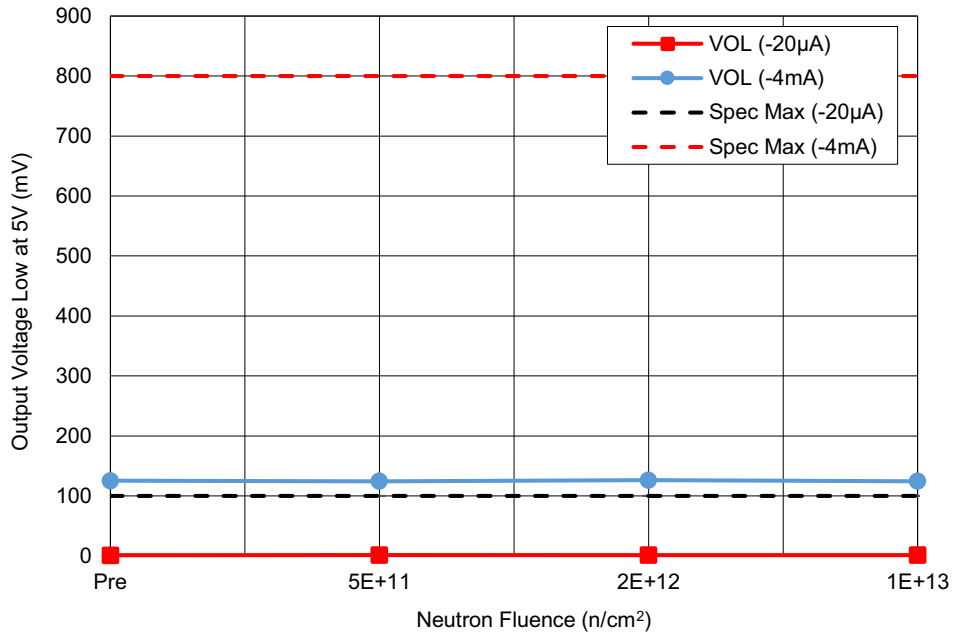


Figure 7. ISL71610x average output voltage low (V_{OL}) with $V_{DD} = 5V$ and $I_{OUT} = -20\mu A$ and $-4mA$ as a function of neutron fluence. The error bars (if visible) represent the minimum and maximum measured values. The datasheet limit is 100mV maximum for $-20\mu A$ and 800mV maximum for $-4mA$.

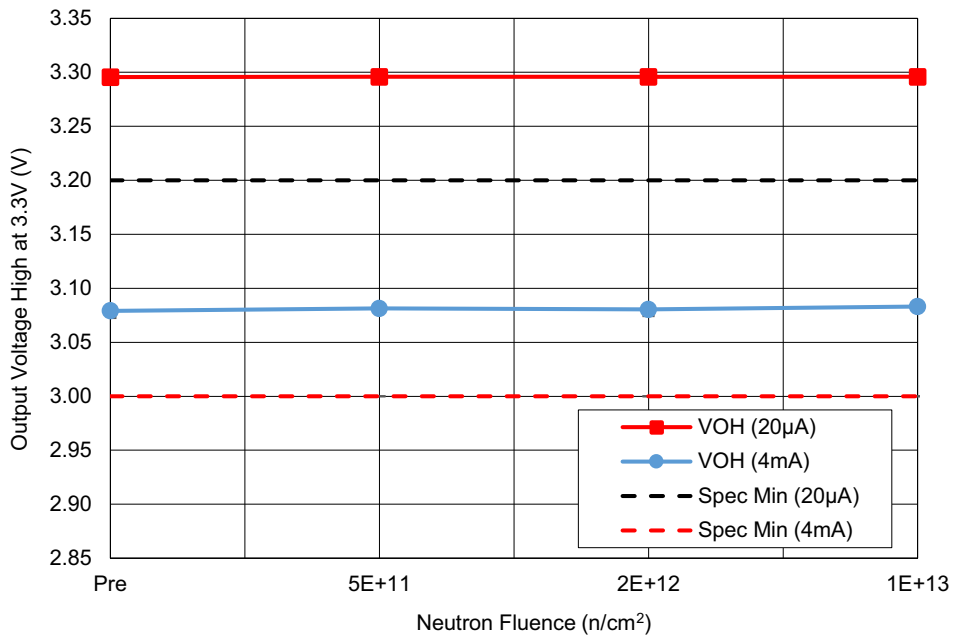


Figure 8. ISL71610x average output voltage high (V_{OH}) with $V_{DD} = 3.3V$ and $I_{OUT} = 20\mu A$ and $4mA$ as a function of neutron fluence. The error bars (if visible) represent the minimum and maximum measured values. The datasheet limit is 3.2V minimum for $20\mu A$ and 3.0V minimum for $4mA$.

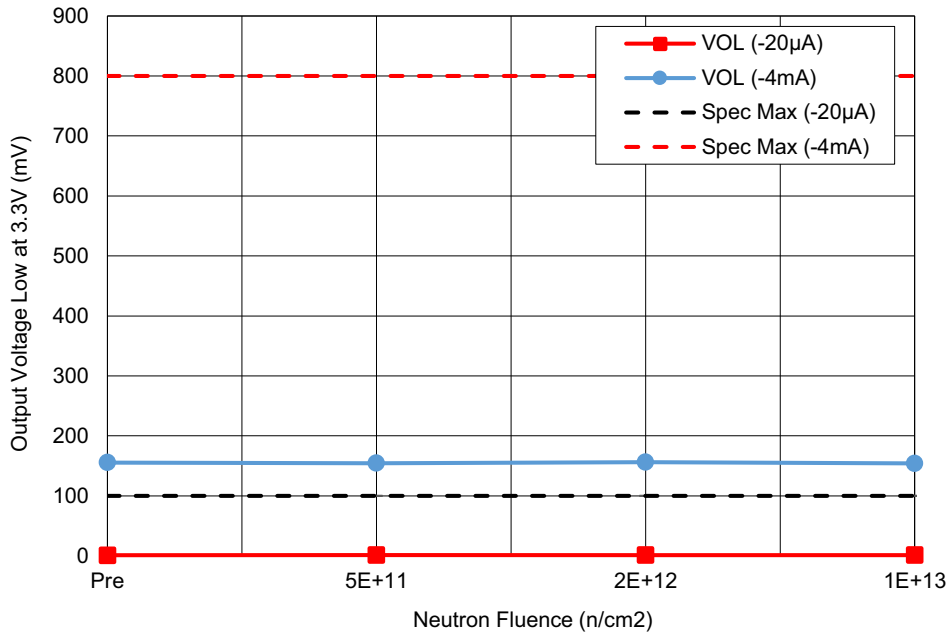


Figure 9. ISL71610x average output voltage low (V_{OL}) with $V_{DD} = 3.3V$ and $I_{OUT} = -20\mu A$ and $-4mA$ as a function of neutron fluence. The error bars (if visible) represent the minimum and maximum measured values. The datasheet limit is 100mV maximum for $-20\mu A$ and 800mV maximum for $-4mA$.

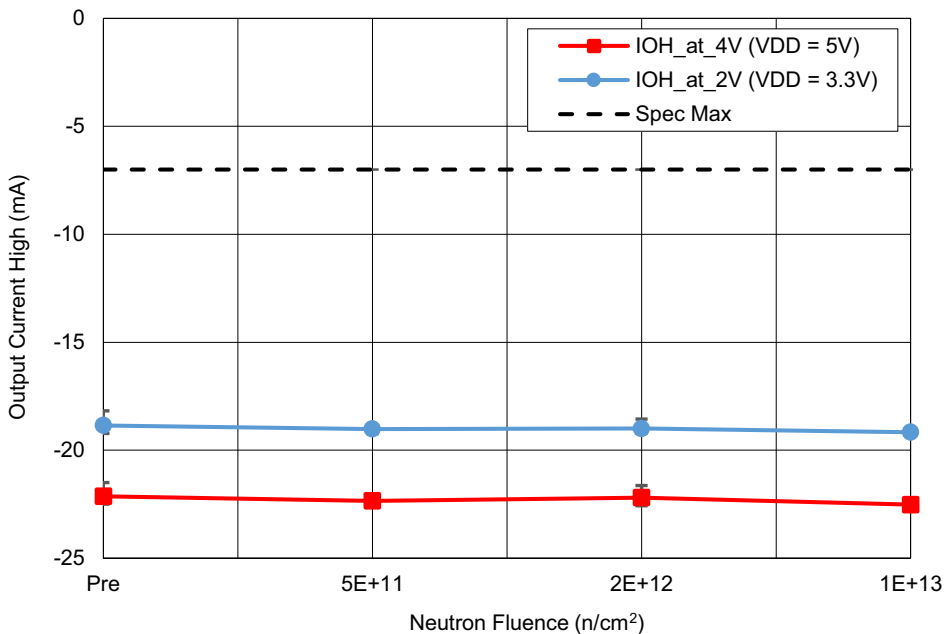


Figure 10. ISL71610x average logic high output drive current (I_{OH}) with $V_{DD} = 3.3V$ and $5V$ as a function of neutron fluence. The error bars represent the minimum and maximum measured values. The datasheet limit is $-7.0mA$ maximum.

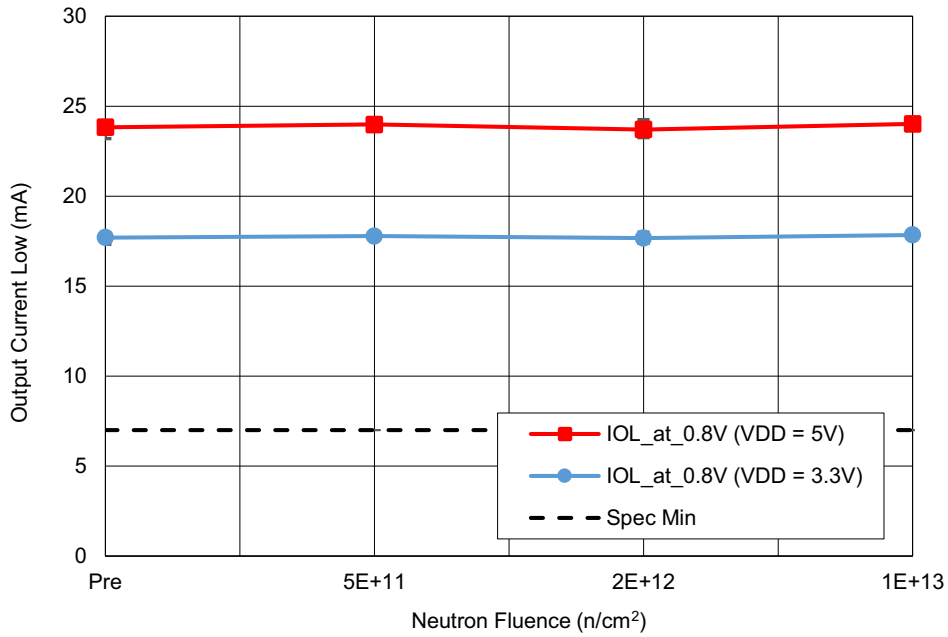


Figure 11. ISL71610x average logic low output drive current (I_{OL}) with $V_{DD} = 3.3V$ and $5V$ as a function of neutron fluence. The error bars represent the minimum and maximum measured values. The datasheet limit is $7.0mA$ minimum.

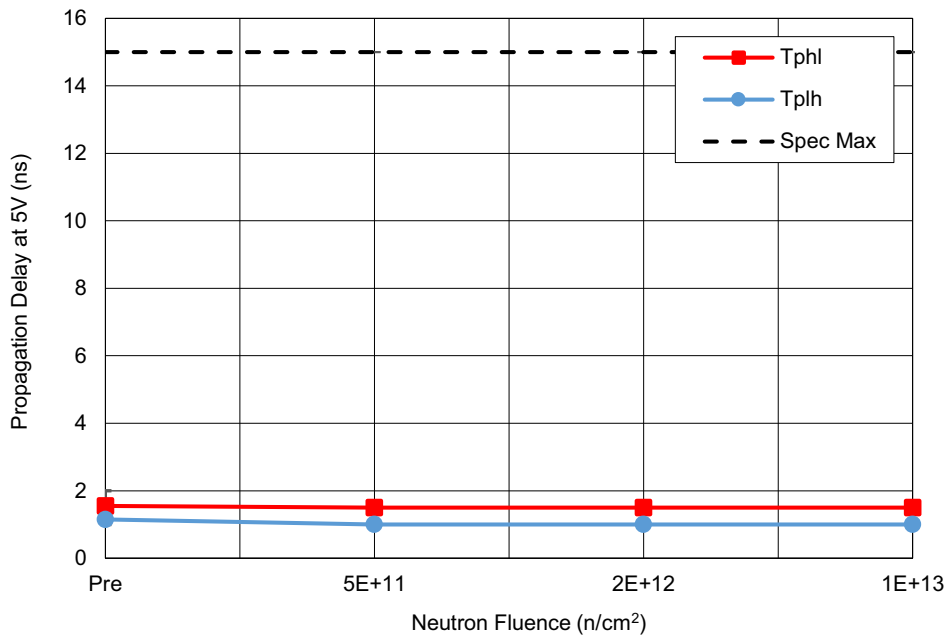


Figure 12. ISL71610x average propagation delay (t_{PHL} , t_{PLH}) with $V_{DD} = 5V$ as a function of neutron fluence. The error bars (if visible) represent the minimum and maximum measured values. The datasheet limit is $15ns$ maximum.

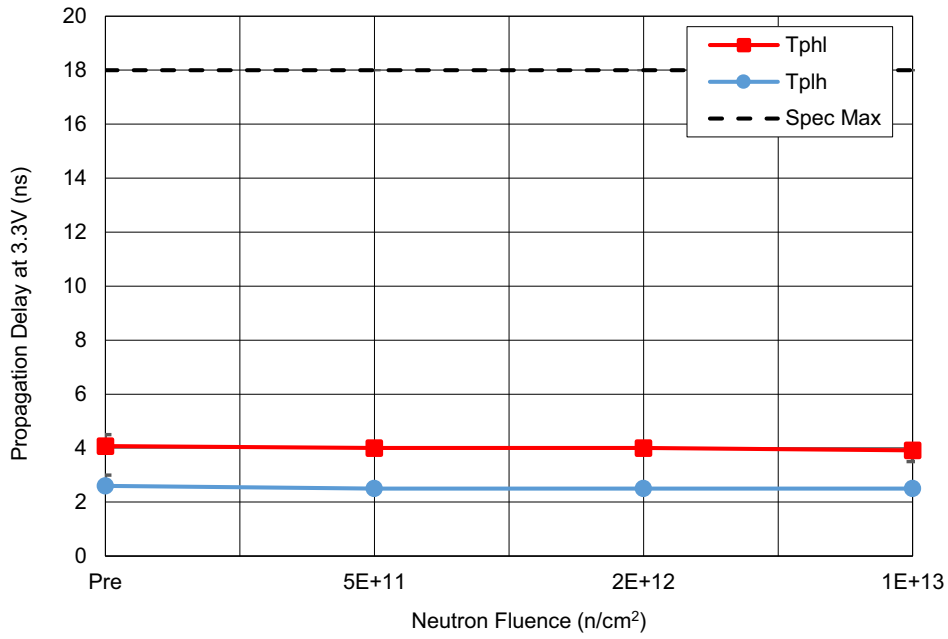


Figure 13. ISL71610x average propagation delay (t_{PHL} , t_{PLH}) with $V_{DD} = 3.3V$ as a function of neutron fluence. The error bars (if visible) represent the minimum and maximum measured values. The datasheet limit is 18ns maximum.

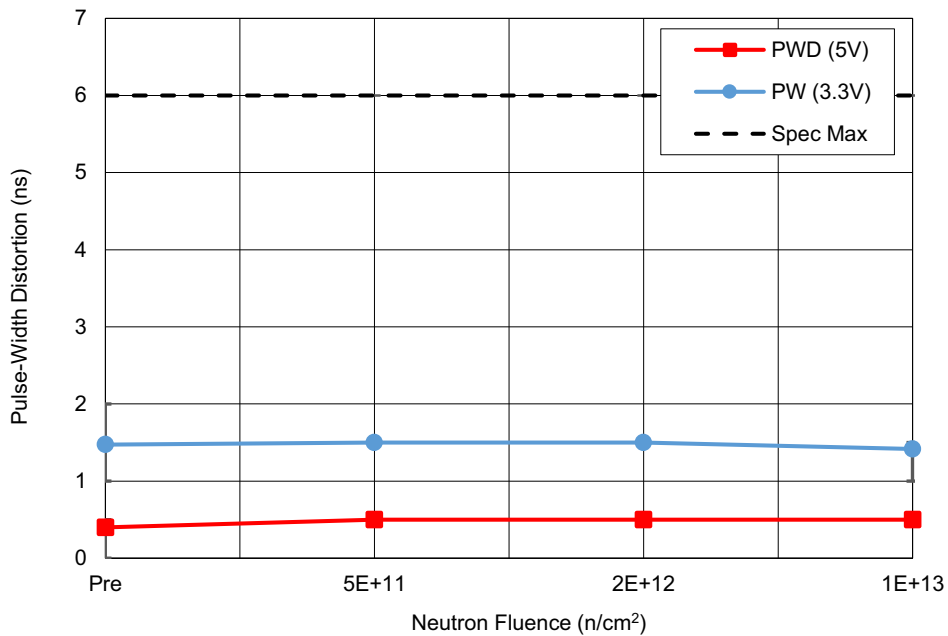


Figure 14. ISL71610x average pulse width distortion (PWD) as a function of neutron fluence. The error bars represent the minimum and maximum measured values. The datasheet limit is 6ns maximum.

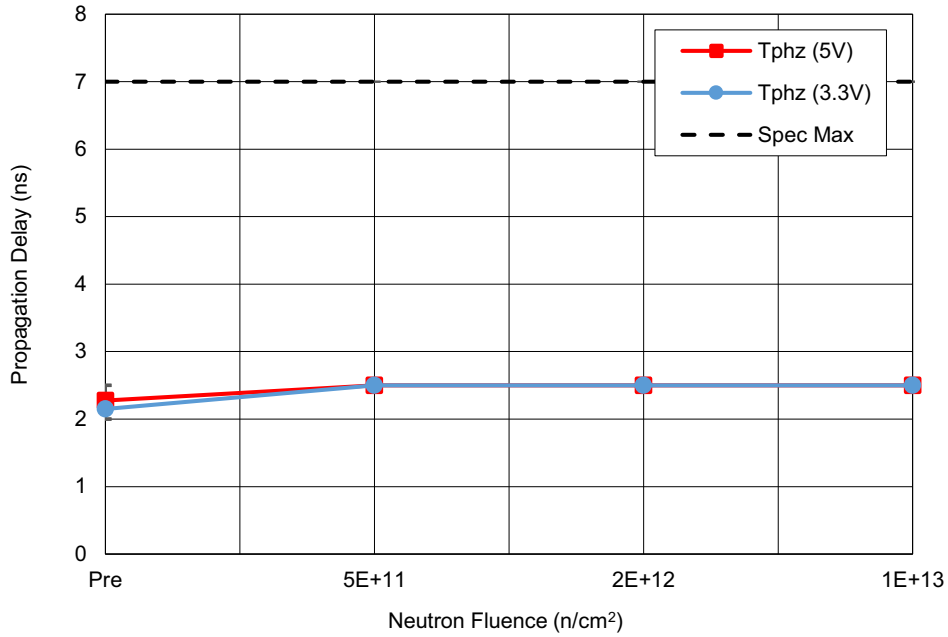


Figure 15. ISL71610x average enable to output propagation delay, high-to-high impedance (t_{PHZ}) with V_{DD} = 3.3V and 5V as a function of neutron fluence. The error bars (if visible) represent the minimum and maximum measured values. The datasheet limit is 7ns maximum.

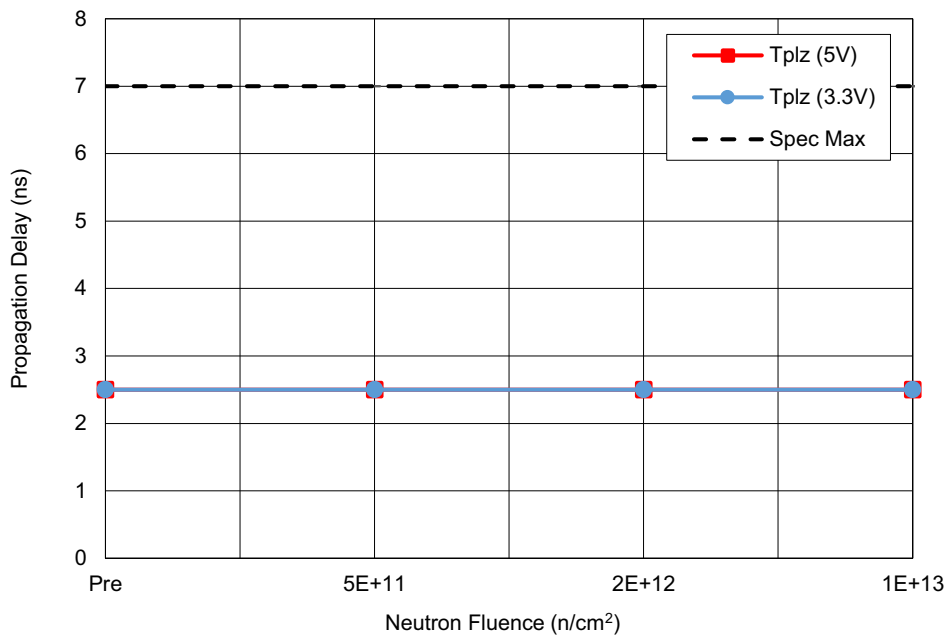


Figure 16. ISL71610x average enable to output propagation delay, low-to-high impedance (t_{PLZ}) with V_{DD} = 3.3V and 5V as a function of neutron fluence. The error bars (if visible) represent the minimum and maximum measured values. The datasheet limit is 7ns maximum.

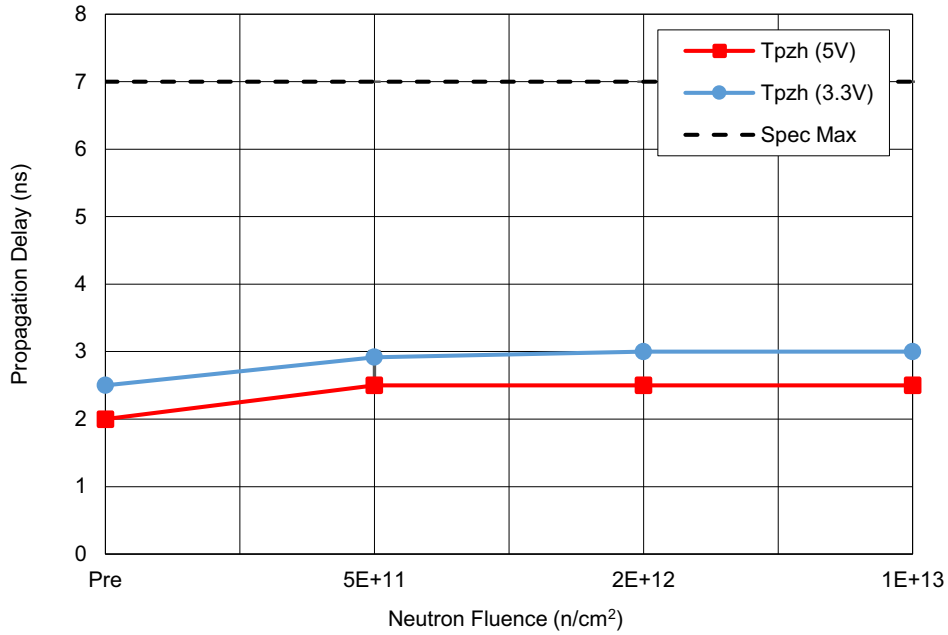


Figure 17. ISL71610x average enable to output propagation delay, high impedance-to-high (t_{pZH}) with $V_{DD} = 3.3V$ and $5V$ as a function of neutron fluence. The error bars (if visible) represent the minimum and maximum measured values. The datasheet limit is 7ns maximum.

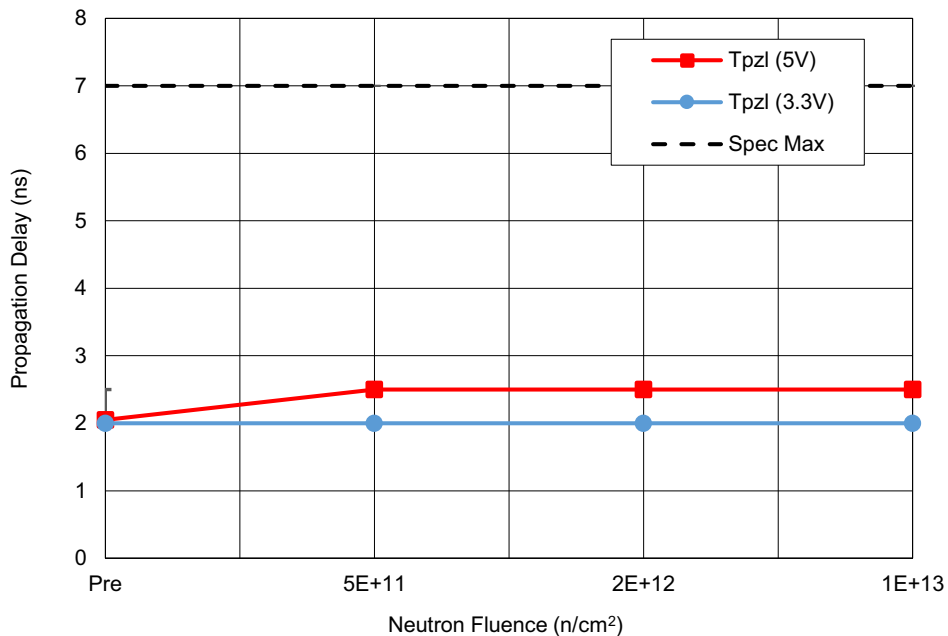


Figure 18. ISL71610x average enable to output propagation delay, high impedance-to-low (t_{pZL}) with $V_{DD} = 3.3V$ and $5V$ as a function of neutron fluence. The error bars (if visible) represent the minimum and maximum measured values. The datasheet limit is 7ns maximum.

3. Discussion and Conclusion

The 1MeV equivalent neutron testing of the ISL71610x radiation tolerant passive-input digital isolator was reported. Parts were tested at actual fluences of $5.30 \times 10^{11} \text{n/cm}^2$, $2.33 \times 10^{12} \text{n/cm}^2$, and $1.04 \times 10^{13} \text{n/cm}^2$. The results of key parameters before and after irradiation to each level are plotted in [Figure 2](#) through [Figure 18](#). The plots show the mean of each parameter as a function of neutron irradiation, with error bars representing the minimum and maximum measured values. The figures also show the applicable electrical limits taken from the datasheet.

Note: These limits are provided for guidance only as the ISL71610x is not specified for the neutron environment.

All samples passed the datasheet limits with little to no degradation after all exposures up to and including $1.04 \times 10^{13} \text{n/cm}^2$.

4. Revision History

| Revision | Date | Description |
|----------|--------------|------------------|
| 1.00 | May 10, 2023 | Initial release. |

A. Appendix

A.1 Reported Parameters

Table 4 lists the key parameters that are considered indicative of part performance. These parameters are plotted in Figure 2 through Figure 18. All limits are taken from the ISL71610SLHMBZ/ISL71610MBZ datasheets.

Table 4. ISL71610x Key Parameters ($T_A = 25^\circ\text{C}$)

| Fig. | Parameter | Symbol | Conditions | Low Limit | High Limit | Unit |
|------|---|-----------------------|---|-----------|------------|----------|
| 2 | Coil Input Resistance | R_{COIL} | $V_{\text{DD}} = 3.0 - 5.5\text{V}$ | 47 | 112 | Ω |
| 3 | DC High Input Threshold | $I_{\text{INH-DC}}$ | Single-ended circuit, $V_{\text{DD}} = 4.5 - 5.5\text{V}$ | 0.5 | - | mA |
| | | $I_{\text{INH-DIFF}}$ | Differential circuit, $V_{\text{DD}} = 3.0 - 5.5\text{V}$, $C_{\text{BOOST}} = 0\text{pF}$ | | | |
| 4 | DC Low Input Threshold | $I_{\text{INL-DC}}$ | Single-ended circuit, $V_{\text{DD}} = 4.5 - 5.5\text{V}$ | - | 8 | mA |
| | | $I_{\text{INL-DIFF}}$ | Differential Circuit, $V_{\text{DD}} = 3.0 - 5.5\text{V}$, $C_{\text{BOOST}} = 0\text{pF}$ | | | |
| 5 | Quiescent Current | I_{DDQ} | $V_{\text{DD}} = 5.0\text{V}$, $\text{IN+} = \text{IN-} = \text{OPEN}$ | - | 3 | mA |
| | | | $V_{\text{DD}} = 3.3\text{V}$, $\text{IN+} = \text{IN-} = \text{OPEN}$ | - | 2 | |
| 6 | Logic High Output Voltage | V_{OH} | $V_{\text{DD}} = 5\text{V}$, $I_{\text{OUT}} = 20\mu\text{A}$ | 4.9 | - | V |
| | | | $V_{\text{DD}} = 5\text{V}$, $I_{\text{OUT}} = 4\text{mA}$ | 4.6 | - | |
| 7 | Logic Low Output Voltage | V_{OL} | $V_{\text{DD}} = 5\text{V}$, $I_{\text{OUT}} = -20\mu\text{A}$ | - | 0.1 | V |
| | | | $V_{\text{DD}} = 5\text{V}$, $I_{\text{OUT}} = -4\text{mA}$ | - | 0.8 | |
| 8 | Logic High Output Voltage | V_{OH} | $V_{\text{DD}} = 3.3\text{V}$, $I_{\text{OUT}} = 20\mu\text{A}$ | 3.2 | - | V |
| | | | $V_{\text{DD}} = 3.3\text{V}$, $I_{\text{OUT}} = 4\text{mA}$ | 3.0 | - | |
| 9 | Logic Low Output Voltage | V_{OL} | $V_{\text{DD}} = 3.3\text{V}$, $I_{\text{OUT}} = -20\mu\text{A}$ | - | 0.1 | V |
| | | | $V_{\text{DD}} = 3.3\text{V}$, $I_{\text{OUT}} = -4\text{mA}$ | - | 0.8 | |
| 10 | Logic High Output Drive Current | I_{OH} | $V_{\text{DD}} = 3.3\text{V}$, 5V | - | -7 | mA |
| 11 | Logic Low Output Drive Current | I_{OL} | $V_{\text{DD}} = 3.3\text{V}$, 5V | 7 | - | mA |
| 12 | Propagation Delay | t_{PHL} | $V_{\text{DD}} = 5\text{V}$, single-ended circuit, $T_{\text{IR}} = T_{\text{IF}} = 3\text{ns}$, $C_{\text{BOOST}} = C_{\text{OUT}} = 16\text{pF}$, $R_{\text{OUT}} = 1\text{k}\Omega$ | - | 15 | ns |
| | | t_{PLH} | | | | |
| 13 | Propagation Delay | t_{PHL} | $V_{\text{DD}} = 3.3\text{V}$, single-ended circuit, $T_{\text{IR}} = T_{\text{IF}} = 3\text{ns}$, $C_{\text{BOOST}} = C_{\text{OUT}} = 16\text{pF}$, $R_{\text{OUT}} = 1\text{k}\Omega$ | - | 18 | ns |
| | | t_{PLH} | | | | |
| 14 | Pulse Width Distortion | PWD | $V_{\text{DD}} = 3.3\text{V}$, 5V , single-ended circuit, $T_{\text{IR}} = T_{\text{IF}} = 3\text{ns}$, $C_{\text{BOOST}} = C_{\text{OUT}} = 16\text{pF}$, $R_{\text{OUT}} = 1\text{k}\Omega$ | - | 6 | ns |
| 15 | Propagation Delay Enable to Output (High-to-High Impedance) | t_{PHZ} | $V_{\text{DD}} = 3.3\text{V}$, 5V , $C_{\text{L}} = 15\text{pF}$ | - | 7 | ns |
| 16 | Propagation Delay Enable to Output (Low-to-High Impedance) | t_{PLZ} | $V_{\text{DD}} = 3.3\text{V}$, 5V , $C_{\text{L}} = 15\text{pF}$ | - | 7 | ns |

Table 4. ISL71610x Key Parameters ($T_A = 25^\circ\text{C}$) (Cont.)

| Fig. | Parameter | Symbol | Conditions | Low Limit | High Limit | Unit |
|------|---|-----------|--|-----------|------------|------|
| 17 | Propagation Delay Enable to Output (High Impedance-to-High) | t_{PZH} | $V_{DD} = 3.3\text{V}, 5\text{V}, C_L = 15\text{pF}$ | - | 7 | ns |
| 18 | Propagation Delay Enable to Output (High Impedance-to-Low) | t_{PZL} | $V_{DD} = 3.3\text{V}, 5\text{V}, C_L = 15\text{pF}$ | - | 7 | ns |

A.2 Related Information

For a full list of related documents, visit our website:

- [ISL71610SLHM](#) and [ISL71610M](#) device pages
- MIL-STD-883 Test Method 1017

IMPORTANT NOTICE AND DISCLAIMER

RENESAS ELECTRONICS CORPORATION AND ITS SUBSIDIARIES (“RENESAS”) PROVIDES TECHNICAL SPECIFICATIONS AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING, WITHOUT LIMITATION, ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for developers skilled in the art designing with Renesas products. You are solely responsible for (1) selecting the appropriate products for your application, (2) designing, validating, and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Renesas grants you permission to use these resources only for development of an application that uses Renesas products. Other reproduction or use of these resources is strictly prohibited. No license is granted to any other Renesas intellectual property or to any third party intellectual property. Renesas disclaims responsibility for, and you will fully indemnify Renesas and its representatives against, any claims, damages, costs, losses, or liabilities arising out of your use of these resources. Renesas' products are provided only subject to Renesas' Terms and Conditions of Sale or other applicable terms agreed to in writing. No use of any Renesas resources expands or otherwise alters any applicable warranties or warranty disclaimers for these products.

(Disclaimer Rev.1.0 Mar 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,
Koto-ku, Tokyo 135-0061, Japan
www.renesas.com

Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit:
www.renesas.com/contact/

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.